

NTK3142P

Small Signal MOSFET

–20 V, –280 mA, P–Channel with ESD Protection, SOT–723

Features

- Enables High Density PCB Manufacturing
- 44% Smaller Footprint than SC–89 and 38% Thinner than SC–89
- Low Voltage Drive Makes this Device Ideal for Portable Equipment
- Low Threshold Levels, 1.8 V $R_{DS(on)}$ Rating
- Low Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migration to Lower Levels Using the Same Basic Topology.
- This is a Pb–Free Device

Applications

- Interfacing, Switching
- High Speed Switching
- Cellular Phones, PDA's

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	–20	V
Gate-to-Source Voltage			V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	–260	mA
		$T_A = 85^{\circ}\text{C}$		–185	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		–280	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	400	mW
				$t \leq 5\text{ s}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	–215	mA
		$T_A = 85^{\circ}\text{C}$		–155	
Power Dissipation (Note 2)			$T_A = 25^{\circ}\text{C}$	P_D	280
Pulsed Drain Current	$t_p = 10\text{ }\mu\text{s}$		I_{DM}	–310	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	–55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode) (Note 2)			I_S	–240	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface–mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface–mounted on FR4 board using the minimum recommended pad size.

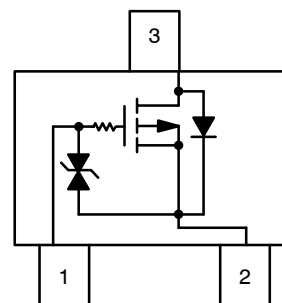


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
–20 V	2.7 Ω @ –4.5 V	–280 mA
	4.1 Ω @ –2.5 V	
	6.1 Ω @ –1.8 V	

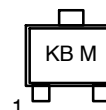
SOT–723 (3–LEAD)



Top View
1 – Gate
2 – Source
3 – Drain

MARKING DIAGRAM


CASE 631AA
SOT–723



KB = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTK3142PT1G	SOT–723 (Pb–Free)	4000/Tape & Reel 4 mm Pitch
NTK3142PT5G	SOT–723 (Pb–Free)	8000/Tape & Reel 2 mm Pitch

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	315	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)	$R_{\theta JA}$	250	
Junction-to-Ambient – Steady State Minimum Pad (Note 4)	$R_{\theta JA}$	440	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
 4. Surface-mounted on FR4 board using the minimum recommended pad size.

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -100\text{ }\mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -100\text{ }\mu\text{A}$, Reference to 25°C		14		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$	$T_J = 25^\circ\text{C}$		-1.0	μA
			$T_J = 125^\circ\text{C}$		-2.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 1	μA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1.3	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-2.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -260\text{ mA}$		2.9	4.0	Ω
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -10\text{ mA}$		2.7	3.4	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -1\text{ mA}$		4.1	5.3	
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ mA}$		6.1	10	
Forward Transconductance	g_{FS}	$V_{DS} = -5\text{ V}, I_D = -10\text{ mA}$		73		mS

CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -10\text{ V}$		15.3		pF
Output Capacitance	C_{OSS}			4.3		
Reverse Transfer Capacitance	C_{RSS}			2.3		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -5\text{ V}, I_D = -100\text{ mA}, R_G = 6\text{ }\Omega$		8.4	16	ns
Rise Time	t_r			15.3	28	
Turn-Off Delay Time	$t_{d(OFF)}$			37.5	80	
Fall Time	t_f			22.7	43	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -10\text{ mA}$	$T_J = 25^\circ\text{C}$	0.69	-1.2	V
			$T_J = 125^\circ\text{C}$	0.56		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, V_{DD} = -20\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}, I_S = -1.0\text{ A}$		37	80	ns
Charge Time	t_a			15.9	30	
Discharge Time	t_b			21.1	50	
Reverse Recovery Charge	Q_{RR}			20	70	nC

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

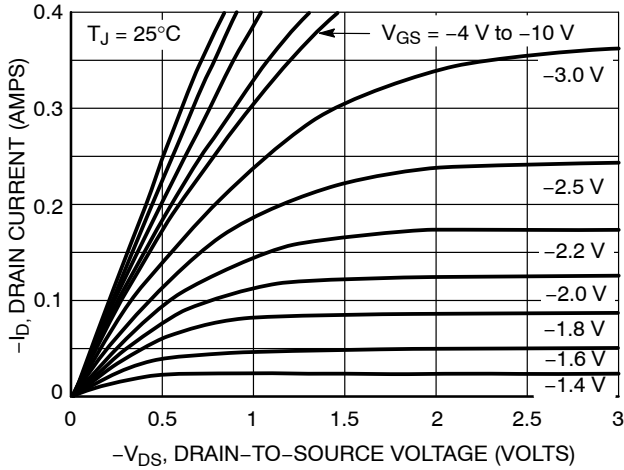


Figure 1. On-Region Characteristics

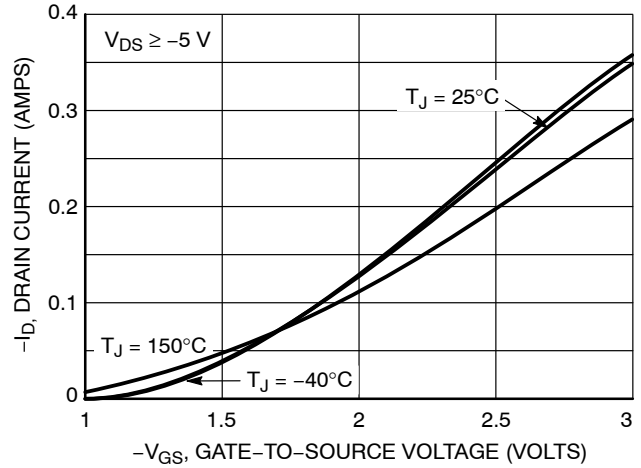


Figure 2. Transfer Characteristics

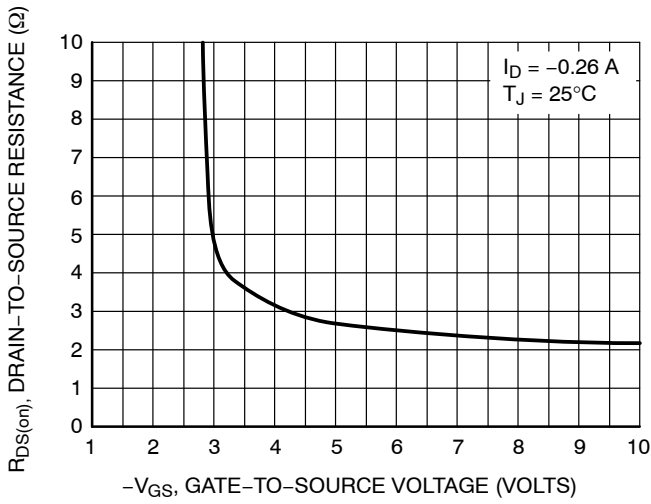


Figure 3. On-Resistance vs. Gate-to-Source Voltage

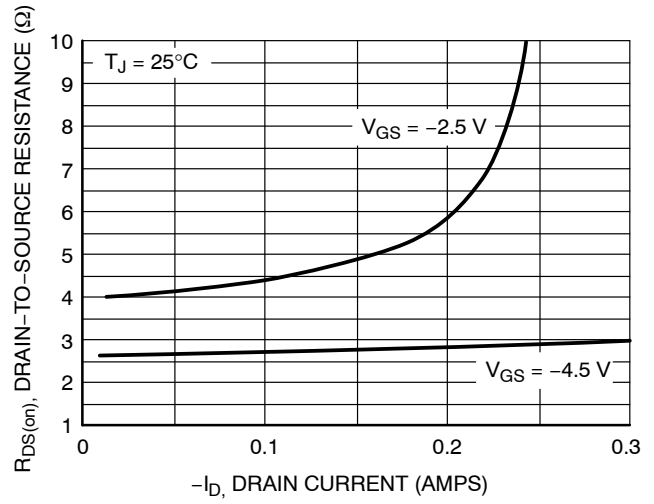


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

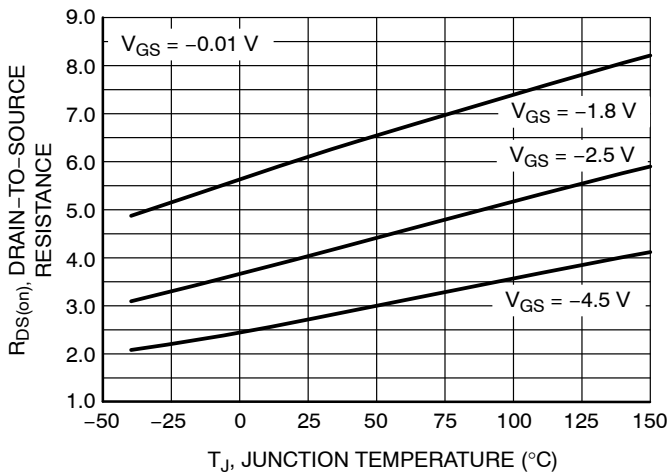


Figure 5. On-Resistance Variation with Temperature

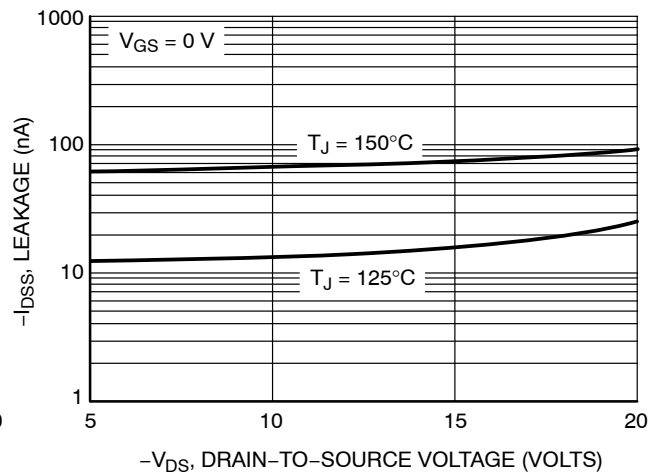


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

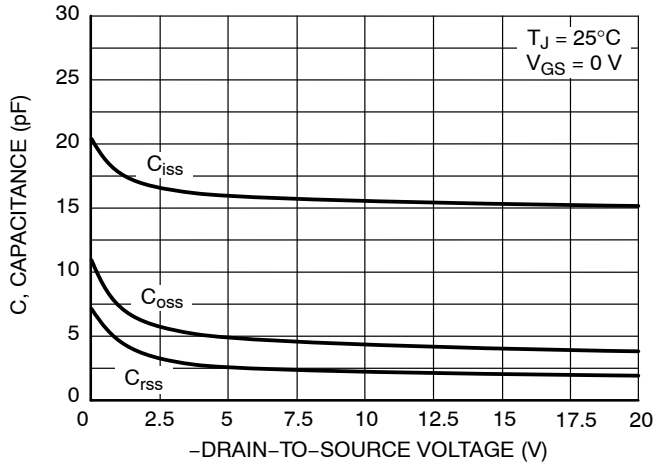


Figure 7. Capacitance Variation

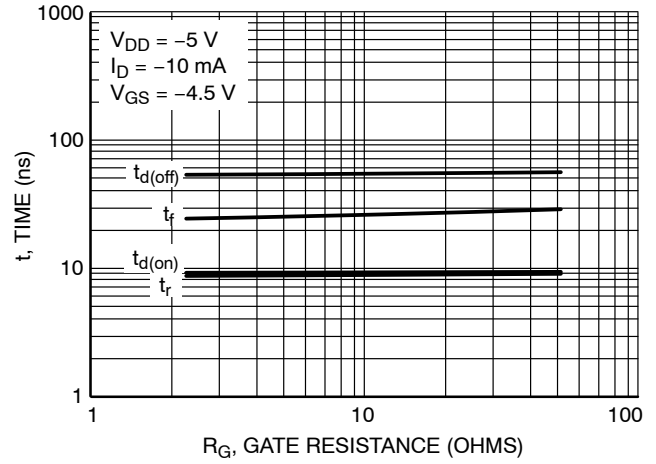


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

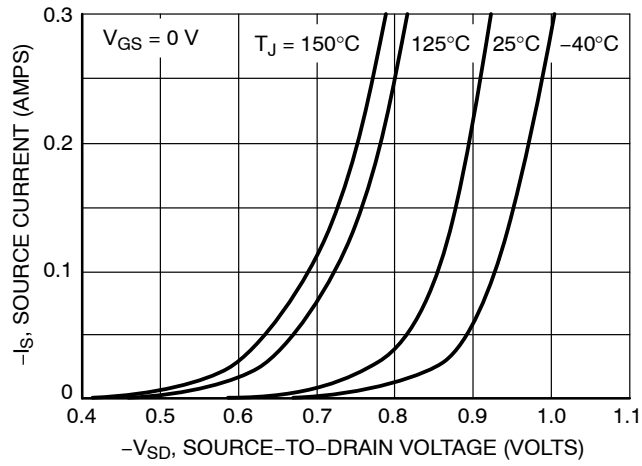
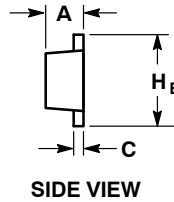
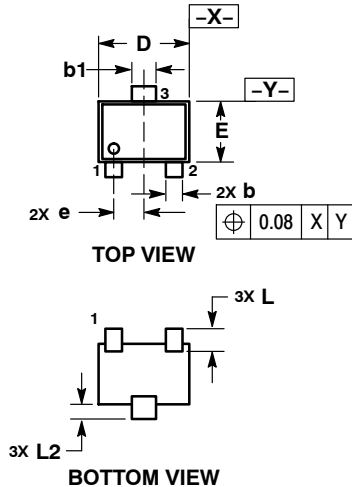


Figure 9. Diode Forward Voltage vs. Current

NTK3142P

PACKAGE DIMENSIONS

SOT-723
CASE 631AA-01
ISSUE D



NOTES:

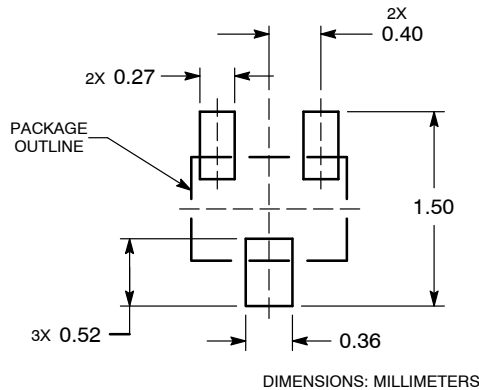
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 3:

- PIN 1. ANODE
2. ANODE
3. CATHODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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